IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Angelo VISCONTI Serial No. 10/782,725

Filed: February 19, 2004

: Atty. Docket: 02-AG-210/EV

: Group Art Unit: 2186

: Confirmation No. 3423

For: METHOD OF PROGRAMMING A MULTI-LEVEL, ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY

INFORMATION DISCLOSURE STATEMENT

Mail Stop Missing Parts Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

The attached Form PTO-1449 provides a listing of information which may be relevant to the subject application. This IDS is not intended as a representation that better art is not available, nor that other art than that identified exists; nor that the information provided is prior art; nor that a search has been made.

This IDS is submitted under:	
XX 37 CFR 1.97(b) - No Fee.	
37 CFR 1.97(c) - No Fee, with Certification.	
37 CFR 1.97(c) - Fee.	
37 CFR 1.97(d) - Fee, Certification & Petitic	on.

The Commissioner is authorized to charge any required fees under 37 CFR 1.17(p) and (i) (1) to Deposit Account No. 50-1556.

Respectfully submitted,

Jose Gutmar

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CERTIFICATE OF MAILING

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List of Documents Cited by Applicant (Use several sheets if necessary) Atty. Docket: 02-AG-210/EV

Applicant: Angelo VISCONTI

Filing Date: February 19, 2004

Serial No. 10/782,725

Group: 2186

U.S. PATENT DOCUMENTS										
Ex'rs In'i		Document Number	Date	•		Name	Class	Sub- class	Filing Date, if applicable	
	AA1	5,926,409	July 20, 199	9	Engh et al.					
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FOREIGN PATENT DOCUMENTS										
<u>-</u>	-	Document Number			Country		Class	Sub- class	Transl'n Yes/No	
	AA2	EP 0 763 828	0 763 828 March 19, 1		Europe				Yes	
	AA3	EP 0 908 895	April 14, 199	9	Europe				Yes	
	AA4	WO 01/63613	0 01/63613 August 30, 2		PCT				Yes	
		ОТН	ER DOC	JMENT	S (Including A	uthor, Title, Date, Pertiner	nt Pages, Etc	.)		
,	AA5			ptimized Programming of Multilevel Flash Eeproms", ICECS 2001: 8 th IEEE International cs, Circuits and Systems, Vol. 2, September 2, 2001, pp. 945-948, XP010563149.						
	AA6 David Esseni et al., "Trading-Off Programming Speed and Current Absorption in Flash Memories with the Ramped-Gate Programming Technique, IEEE Transactions on Electron Devices, Vol. 47, No. 4, April 2000, pp. 828-834, XP00113105								he Ramped-Gate	
	AA7 European Search Report dated July 25, 2003 for European Application No. 03425096.9.									
Examiner:				Date (Date Considered:					
EXAMIN	ER: Initia	if reference cons	idered whethe	er or not ci	tation is in confo	rmance with MPEP 600: I	Draw line thro	ush sitetiee	if not in	

conformance and not considered. Include copy of this form with next communication to applicant.